

Application No. 10/680,464
Response to OA of 07/08/2005

Amendments to the Claims

This listing of claims will replace all prior versions, and listings, of the claims:

1. (currently amended) A magnetic memory comprising:
 - a first line having a first cross-sectional area;
 - a second line having a second cross-sectional area different than the first cross-sectional area; and
 - a magnetic memory cell stack positioned between the first line and the second line, wherein the first and second lines are T-shaped.
2. (original) The memory of claim 1, where the first line is defined as a word line.
3. (original) The memory of claim 1, where the first cross-sectional area is greater than the second cross-sectional area.
4. (currently amended) The memory of claim 1, where the first line further comprises:
 - a first region having a first region cross-sectional area;
 - a second region located adjacent the magnetic memory cell stack, the second region having a second region cross-sectional area, the second region cross-sectional area being smaller than the first region cross-sectional area.
5. (original) The memory of claim 4, wherein the second region cross-sectional area is substantially similar to the second cross-sectional area.
6. (original) The memory of claim 4, where the first region has a first width and the second region has a second width smaller than the first width.
7. (original) The memory of claim 6, wherein the first region is substantially rectangular shaped, and the second region is substantially rectangular shaped.

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8. (canceled)

9. (currently amended) A magnetic memory comprising:

a magnetic memory cell stack;
a first magnetic memory line for carrying a current, located adjacent the magnetic memory cell stack, the first magnetic memory line including a first region with a first width and a second region with a second width smaller than the first width; and
a second magnetic memory line for carrying a current, located adjacent the magnetic memory cell stack, the second magnetic memory line including a third region sized with the first width and a fourth region sized with the second width.

10. (currently amended) The magnetic memory of claim 9, wherein the first and second magnetic memory lines includes at least a partial outer layer for localizing a magnetic field at the magnetic memory cell stack.

11. (original) The magnetic memory of claim 10, wherein the outer layer is a cladding layer.

12. (currently amended) The magnetic memory of claim 9, wherein the first and second magnetic memory lines are, including the first section and the second section, is substantially T-shaped.

13. – 17. (canceled)

18. (currently amended) A magnetic memory cell, comprising:

a first line having a first width and a second width, where the first width is greater than the second width; and
a memory cell stack having a first side adjacent the first line along the second width; and

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a second line having a third width and a fourth width, wherein the third width is greater than the fourth width and the memory cell stack is adjacent the second line along the fourth width.

19. (canceled)

20. (canceled)

21. (currently amended) The magnetic memory cell of claim 18-20, wherein the second width and the fourth width are the same as widths of the memory cell stack.

22. (currently amended) The magnetic memory cell of claim 18-20, wherein the second width is the same as the fourth width.

23. (currently amended) The magnetic memory cell of claim 18-20, further comprising means for localizing and focusing magnetic fields produced by currents passed through the first line and the second line, where the magnetic fields are localized around the first line and the second line and focused into the memory cell stack.

24. (currently amended) The magnetic memory cell of claim 18-20, further comprising cladding around the first line and cladding around the second line, where the cladding is substantially away from between the first line and the memory cell stack and the second line and the memory cell stack.

25. (original) The magnetic memory cell of claim 18, wherein the second width is the same as a width of the memory cell stack.

26. (original) The magnetic memory cell of claim 18, further comprising means for localizing and focusing a magnetic field where the magnetic field is localized around the first line and focused into the memory cell stack.

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27. (original) The magnetic memory cell of claim 18, further comprising cladding around the first line and away from between the first line and the memory cell stack.
28. (currently amended) The magnetic memory cell of claim 18, wherein the first and second lines are is a T-shaped conductors.
29. (currently amended) A magnetic memory device, comprising:
an array of magnetic memory cells; and
first lines crossing the array of magnetic memory cells, the first lines having a first section and a second section, where the first section is wider than the second section and
second lines crossing the array of magnetic memory cells, wherein the first and second lines have a T-shaped face.
30. (original) The magnetic memory device of claim 29, wherein the first section is separated from the array of magnetic memory cells by the second section.
31. (original) The magnetic memory device of claim 29, further comprising means for localizing and focusing a magnetic field, where the magnetic field is localized around each first line and focused into the array of magnetic memory cells.
32. (original) The magnetic memory device of claim 29, wherein the first section of one first line is in substantially the same plane as the first section of an adjacent first line.
33. (currently amended) The magnetic memory device of claim 29, wherein the first section has a rectangular face and the second section has a rectangular face, the rectangular face of the first section and the rectangular face of the second section forming the T-shaped face a T-shape.
34. (original) The magnetic memory device of claim 29, wherein the first section of one first line is in substantially a different plane than the first section of an adjacent first line.

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35. (canceled)

36. (currently amended) The magnetic memory device of claim 29-35, wherein the first lines and the second lines are orthogonal.

37. - 42. (canceled)